

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (currently amended): An organic light emitting diode device comprising: a substrate, a layer of organic light emitting material, a transparent cathode comprising a layer of material with a work function less than 4 eV, a passivation layer comprising boron oxide overlying said cathode, ~~and~~ an encapsulation layer comprising a dielectric oxide directly overlying said passivation layer, and sealing layers of adhesive and glass.

Claim 2 (canceled).

Claim 3 (previously presented): A device according to claim 1, wherein said material with a work function of less than 4 eV comprises calcium.

Claims 4-8 (canceled).

Claim 9 (currently amended): A method of manufacturing an organic light emitting diode device, comprising the steps of: (a) taking a substrate bearing a layer of organic light emitting material and a transparent cathode comprising a layer of material with a work function less than 4 eV; (b) depositing a passivation layer comprising boron oxide on said cathode; ~~and~~

(c) depositing an encapsulating layer comprising a dielectric oxide directly on said passivation layer; and (d) sealing the device with an adhesive and glass.

Claim 10 (original): A method according to claim 9, wherein said passivation layer is deposited by thermal evaporation.

Claims 11-19 (canceled).

Claim 20 (previously presented): A device according to claim 1, wherein said light emitting material is a polymeric light emitting material.

Claim 21 (previously presented): A device according to claim 1, wherein said passivation layer directly overlies said layer of material with a work function less than 4 eV.

Claim 22 (canceled).

Claim 23 (currently amended): A device according to claim 1, wherein said dielectric oxide of said encapsulating layer ~~comprises a dielectric oxide~~ is selected from a group consisting of Al₂O₃, SiO₂, TiO₂, ZrO₂, MgO, HfO₂, Ta₂O₅, aluminum titanium oxide, and tantalum hafnium oxide.

Claim 24 (canceled).

Claim 25 (currently amended): A device according to claim [24] 1, wherein said adhesive comprises epoxy resin.

Claim 26 (canceled).

Claim 27 (previously presented): A method according to claim 9, wherein said passivation layer is deposited directly onto said layer of material with a work function less than 4 eV.

Claim 28 (canceled).

Claim 29 (currently amended): A method according to claim 9, wherein said dielectric oxide of said encapsulating layer ~~comprises a dielectric oxide~~ is selected from a group consisting of Al_2O_3 , SiO_2 , TiO_2 , ZrO_2 , MgO , HfO_2 , Ta_2O_5 , aluminum titanium oxide, and tantalum hafnium oxide.

Claim 30 (previously presented): A method according to claim 9, wherein said encapsulating layer is deposited by electron beam evaporation.

Claim 31 (previously presented): A method according to claim 9, wherein said encapsulating layer is deposited by sputtering.

Claim 32 (canceled).

Claim 33 (previously presented): A method according to claim 9, comprising the step of adapting the thickness of said passivation layer to energy of electrons, ions, or fields from which protection is required.

Claim 34 (previously presented): A device according to claim 1, wherein said passivation layer consists of boron oxide and provides a function of absorbing electrons, ions, and electric fields harmful to said transparent cathode thereby protecting said transparent cathode.

Claim 35 (canceled).

Claim 36 (currently amended): A device according to claim [35] 1, wherein said material with a work function of less than 4 eV comprises calcium, and wherein said light emitting material is a polymeric light emitting material.

Claim 37 (canceled).

Claim 38 (new): A device according to claim 1, wherein said dielectric oxide of said encapsulating layer is selected from a group consisting of Al_2O_3 , TiO_2 , ZrO_2 , MgO , HfO_2 , Ta_2O_5 , aluminum titanium oxide, and tantalum hafnium oxide.

Claim 39 (new): A method according to claim 9, wherein said dielectric oxide of said encapsulating layer is selected from a group consisting of Al_2O_3 , TiO_2 , ZrO_2 , MgO , HfO_2 , Ta_2O_5 , aluminum titanium oxide, and tantalum hafnium oxide.